STEF12

Datasheet – production data



Features

- Continuous current (typ): 3.6 A
- N-channel on-resistance (typ): 53 mΩ
- Enable/Fault functions
- Output clamp voltage (typ):15 V
- Undervoltage lockout
- Short-circuit limit
- Overload current limit
- Controlled output voltage ramp
- Thermal latch (typ): 165 °C
- Uses tiny capacitors
- Operating junction temp. 40 °C to 125 °C
- Available in DFN10 (3x3 mm) package

Applications

- Hard disk drives
- Solid state drives (SSD)
- Hard disk and SSD arrays
- Set-top boxes
- DVD and Blu-ray disc drivers

Description

The STEF12 is an integrated electronic fuse optimized for monitoring output current and input voltage. Connected in series to a 12 V rail, it is capable of protecting the electronic circuitry on its output from overcurrent and overvoltage. The device has a controlled delay and turn-on time. When an overload condition occurs, the STEF12 limits the output current to a predefined safe value. If the anomalous overload condition

Table 1.Device summary

Order code	Package	Packaging
STEF12PUR	DFN10 (3x3 mm)	Tape and reel

March 2012

Doc ID 019056 Rev 4

1/20

This is information on a product in full production.



DFN10 (3x3 mm)

persists it goes into an open state, disconnecting the load from the power supply. If a continuous short-circuit is present on the board, when power is re-applied the E-fuse initially limits the output current to a safe value and then again goes into an open state. The device is equipped with a thermal protection circuit. The intervention of the thermal protection is signalled to the board monitoring circuits through a signal on the Fault pin. Unlike the mechanical fuses, which must be physically replaced after a single event, the Efuse does not degrade in its performance after short-circuit/thermal protection interventions and it is reset either by recycling the supply voltage or using the Enable pin. The companion chip for the 5 V power rails is also available with part number STEF05.

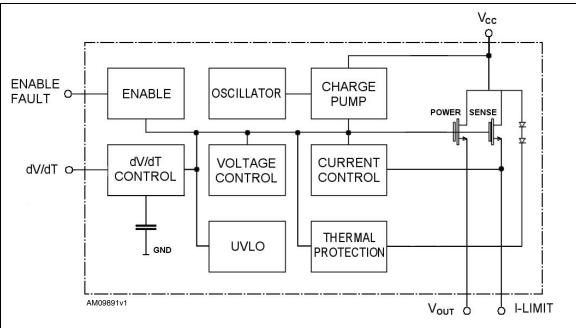


Contents

1	Devic	Device block diagram					
2	Pin c	onfigur	ration				
3	Maxir	num ra	tings				
4	Elect	rical ch	aracteristics6				
5	Туріс	al appl	ication				
	5.1	Operat	ing modes				
		5.1.1	Turn-on				
		5.1.2	Normal operating condition9				
		5.1.3	Output voltage clamp9				
		5.1.4	Current limiting				
		5.1.5	Thermal shutdown9				
	5.2	R limit calculation					
	5.3	C _{dv/dt} c	calculation				
	5.4	Enable	/Fault pin				
6	Туріс	al perfo	ormance characteristics 12				
7	Packa	age me	chanical data				
8	Revision history						



1 Device block diagram







2 Pin configuration

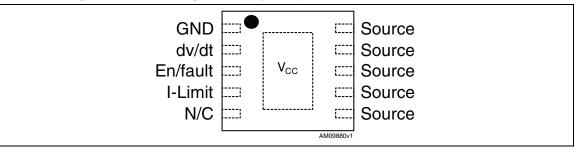


Table 2.	Pin description			
Pin n°	Symbol	Note		
1	GND	Ground pin		
2	dv/dt	The internal dv/dt circuit controls the slew rate of the output voltage at turn-on. The internal capacitor allows a ramp-up time of around 1ms. An external capacitor can be added to this pin to increase the ramp time. If an additional capacitor is not required, this pin should be left open.		
3	En/Fault	The Enable/Fault pin is a tri-state, bi-directional interface. During normal operation the pin must be left floating, or it can be used to disable the output of the device by pulling it to ground using an open drain or open collector device. If a thermal fault occurs, the voltage on this pin goes into an intermediate state to signal a monitor circuit that the device is in thermal shutdown. It can be connected to another device of this family to cause a simultaneous shutdown during thermal events.		
4	I-Limit	A resistor between this pin and the Source pin sets the overload and short-circuit current limit levels.		
5	NC	Not connected		
6 to 10	V _{OUT} /Source	Connected to the source of the internal power MOSFET and to the output terminal of the fuse		
11	V _{CC}	Exposed pad. Positive input voltage must be connected to V _{CC} .		

Table 2. Pin description

4/20



3 Maximum ratings

Symbol	Parameter	Value	Unit
V	Positive power supply voltage (steady state)	-0.3 to 18	v
V _{CC}	Positive power supply voltage (max 100ms)	-0.3 to 25	v
V _{OUT} /source	(max 100ms)	-0.3 to Vcc+0.3	V
I-Limit	(max 100ms)	-0.3 to 25	V
En/Fault		-0.3 to 7	V
dv/dt		-0.3 to 7	V
T _{op}	Operating junction temperature range ⁽¹⁾	-40 to 125	°C
T _{STG}	Storage temperature range	-65 to 150	°C
T _{LEAD}	Lead temperature (soldering) 10 sec	260	°C

Table 3. Absolute maximum ratings

1. The thermal limit is set above the maximum thermal rating. It is not recommended to operate the device at temperatures greater than the maximum ratings for extended periods of time.

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Symbol	Parameter Value		Unit
R _{thJA}	Thermal resistance junction-ambient	52.7	°C/W
R _{thJC}	Thermal resistance junction-case	17.4	°C/W

Table 4. Thermal data

Table 5.ESD performance

Symbol	Parameter	Test conditions	Value	Unit
		HBM	1	kV
ESD	ESD protection	MM	200	V
		CDM	500	V



4 Electrical characteristics

 V_{CC} = 12 V, V_{EN} = 3.3 V, C_I = 10 $\mu\text{F},~C_O$ = 47 $\mu\text{F},~T_J$ = 25 °C (unless otherwise specified).

$\begin{tabular}{ c c c c c c } \hline Under/Overvoltage protection $$V_{CL amp}$ Output clamping voltage $$V_{CC}$ = 18 V$ 13.8 15 16.2 V$ $$V_{UVLO}$ Undervoltage lockout $$Turn-on, voltage rising $$7.7 8.5 9.3 V$ $$V_{Vyyst}$ UVLO hysteresis $$0.80 V$ $$Verwer MOSFET$ $$0.80 0$ V$ $$Power MOSFET$ $$Verwer MOSFET$	Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
$\begin{array}{c c c c c c c } \hline V_{UVLO} & Undervoltage lockout & Turn-on, voltage rising & 7.7 & 8.5 & 9.3 & V \\ \hline V_{Hyst} & UVLO hysteresis & 0.80 & V \\ \hline \hline V_{Hyst} & UVLO hysteresis & 0.80 & V \\ \hline \hline Power MOSFET & & & & & & & & & & & & & & & & & & &$	Under/Ove	ervoltage protection					
$\begin{array}{c c c c c c c } \hline V_{UVLO} & Undervoltage lockout & Turn-on, voltage rising & 7.7 & 8.5 & 9.3 & V \\ \hline V_{Hyst} & UVLO hysteresis & 0.80 & V \\ \hline \hline Power MOSFET \\ \hline \hline I_{dly} & Delay time & Enabling of chip to I_D = 100 mA with a 1 A resistive load & 350 & \mus \\ \hline I_{dly} & Delay time & (1) & 35 & 53 & 70 & 0.80 & V \\ \hline \hline I_{D} & 0^{n-resistance} & (1) & 35 & 53 & 70 & 0.80 & V \\ \hline I_{D} & Continuous current & V_{CC} = 18 V, V_{GS} = 0, R_L = infinite & 40 & 100 & mV \\ \hline I_D & Continuous current & 0.5in^2 pad, T_A = 25 ^{\circ}C ^{(1)} & 3.6 & A & A & A \\ \hline I_{Lim} & Overload current limit & R_{Limit} = 22 ^{\circ}\Omega & 3.3 & 4.4 & 5.5 & A \\ \hline I_{Lim} & Overload current limit & R_{Limit} = 22 ^{\circ}\Omega & 4.4 & A & A & A & A & A & A & A & A & A & $	V _{Clamp}	Output clamping voltage	V _{CC} = 18 V	13.8	15	16.2	V
Power MOSFETtdyDelay timeEnabling of chip to $I_D = 100 \text{ mA}$ with a 1 A resistive load350 μ s R_{DSon} On-resistance(1)355370 A2 $m\Omega$ V_{OFF} Off state output voltage $V_{CC} = 18 \text{ V}, V_{GS} = 0, R_L = infinite$ 400100mV I_D Continuous current $0.5in^2 \text{ pad}, T_A = 25 \text{ °C} (1)$ 3.6A I_D Continuous current $0.5in^2 \text{ pad}, T_A = 25 \text{ °C} (1)$ 3.6A $I_LminitinitinitinitinitinitinitiRLimit = 22 \Omega3.34.45.5AI_LminitinititinitiRLimit = 22 \Omega3.34.45.5AI_LminititinititinitiRLimit = 22 \Omega3.34.45.5AV_{Lm}Overload current limitRLimit = 22 \Omega3.34.45.5AV_{Lm}Overload current limitRLimit = 22 \Omega3.34.45.5AV_{Lm}Output voltage ramp timeEnable to V_{OUT} = 11.7 V, NoC_{dv/dt}0.50.92.6msVILLow level input voltageOutput disabled0.821.41.95VV_{I(NT)}Intermediate level input voltageOutput enabled1.962.643.3VV_{IH}High level input voltageOutput enabled1.962.643.3VV_{I(MAX)}High state maximum voltageOutput enable = 0 V-10-30\muAI_{Link}Low level input current (sink)$		Undervoltage lockout	Turn-on, voltage rising	7.7	8.5	9.3	V
$\begin{tabular}{ c c c c c c } \hline tend below is a 1 A resistive load in the set of the $	V _{Hyst}	UVLO hysteresis			0.80		V
$\begin{tabular}{ c c c c c } \hline \begin{tabular}{ c c c } \hline \begin{tabular}{ c c c } \hline \begin{tabular}{ c c } \hline \hline \begin{tabular}{ c c } \hline $	Power MO	SFET	1		I	I	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	t _{dly}	Delay time			350		μs
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	5		(1)	35	53	70	
$\begin{split} \begin{array}{ c c c c c } \hline l_{D} & \hline l_{A} & \hline l_{D} & \hline l_{D}$	R _{DSon}	On-resistance	- 40 °C < T _J < 125 °C $^{(2)}$			82	mΩ
IbContinuous currentMinimum copper, TA = 80 °C1.7AMinimum copper, TA = 80 °C1.7ACurrent limitRLimit = 22 Ω 3.34.45.5AIbortShort-circuit current limitRLimit = 22 Ω 3.34.45.5AILimOverload current limitRLimit = 22 Ω 3.34.45.5Adv/dt circuitRLimit = 22 Ω 4.4AAdv/dt circuitdv/dt circuitCurrent limitRLimit = 22 Ω 0.50.92.6msEnable for V _{OUT} = 11.7 V, No C _{dv/dt} 0.50.92.6msEnable/FaultVILLow level input voltageOutput disabled0.350.580.81VVILLow level input voltageOutput disabled0.821.41.95VVILHigh level input voltageOutput enabled1.962.643.3VVI(MAX)High state maximum voltageOutput enabled1.962.643.3VILLow level input current (sink)VEnable = 0 V-10-30 μA ILLigh level leakage current for external switchVenable = 3.3 V11 μA ILMaximum fan-out for fault signalTotal numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsIntermediate levelDevice operational1.5	V _{OFF}	Off state output voltage	V_{CC} = 18 V, V_{GS} = 0, R_L = infinite		40	100	mV
UnderstandMinimum copper, $T_A = 80 ^{\circ}\text{C}$ 1.7Current limitIshortShort-circuit current limit $R_{\text{Limit}} = 22 \Omega$ 3.34.45.5AILimOverload current limit $R_{\text{Limit}} = 22 \Omega$ 3.34.45.5Adv/dtOutput current limit $R_{\text{Limit}} = 22 \Omega$ 4.4AAdv/dt circuitEnable to $V_{\text{OUT}} = 11.7 ^{\circ}$, No0.50.92.6msEnable/Fault V_{IL} Low level input voltageOutput disabled0.350.580.81V V_{IL} Low level input voltageOutput disabled0.821.41.95V V_{IL} Low level input voltageOutput enabled1.962.643.3V V_{IL} Low level input voltageOutput enabled1.962.643.3V $V_{\text{I(MAX)}}$ High state maximum voltageOutput enabled1.962.643.3V $V_{\text{I(MAX)}}$ High level leakage current (sink) $V_{\text{Enable} = 0 ^{\circ}$ -10-30 μA I_1 High level leakage current for external switch $V_{\text{Enable} = 3.3 ^{\circ}$ 31 I_1 μA Total numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsDevice operational1.52 I_{Bias} Bias currentDevice operational1.52mA	I	Continuous summent	0.5in ² pad, T _A = 25 °C $^{(1)}$		3.6		_
I ShortShort-circuit current limit $R_{Limit} = 22 \ \Omega$ 3.34.45.5AI I LimOverload current limit $R_{Limit} = 22 \ \Omega$ 4.4AAdv/dt circuitOutput voltage ramp timeEnable to $V_{OUT} = 11.7 \ V, \ No$ $C_{dv/dt}$ 0.50.92.6msEnable/FaultVIL Low level input voltageOutput disabled0.350.580.81V V_{IL} Low level input voltageOutput disabled0.821.41.95V V_{II} High level input voltageOutput enabled1.962.643.3V V_{II} Low level input voltageOutput enabled1.962.643.3V V_{II} High level input voltageOutput enabled1.962.643.3V V_{IIA} High state maximum voltage0.4-10-30 μA I_{IL} Low level input current (sink) $V_{Enable} = 0 \ V$ -10-30 μA I_{I} High level leakage current for external switch $V_{Enable} = 3.3 \ V$ 1 μA 3UnitsTotal numbers of chips that can be connected to this pin for simultaneous shutdown33UnitsTotal numbers of chips that can be connected to this pin for simultaneous shutdown1.52mAInvoice operational1.52mA	۱D	Continuous current	Minimum copper, T _A = 80 °C		1.7		A
LimDefineLimLimAI_LimOverload current limit $R_{Limit} = 22 \Omega$ 4.4Adv/dt circuitdv/dtOutput voltage ramp timeEnable to $V_{OUT} = 11.7 V$, No $C_{dv/dt}$ 0.50.92.6msEnable/Fault V_{IL} Low level input voltageOutput disabled0.350.580.81V V_{IL} Low level input voltageOutput disabled0.350.580.81V V_{IL} Low level input voltageOutput disabled0.821.41.95V V_{IL} High level input voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High state maximum voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High level input current (sink) $V_{Enable} = 0 V$ -10-30 μA I_{I} High level leakage current for external switch $V_{Enable} = 3.3 V$ 1 μA I_{I} Maximum fan-out for fault signalTotal numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsTotal deviceDevice operational1.52 I_{Bias} Bias currentDevice operational1.52	Current lin	nit	· · ·				
dv/dt circuitdv/dtOutput voltage ramp timeEnable to $V_{OUT} = 11.7 \text{ V}$, No $C_{dv/dt}$ 0.50.92.6msEnable/Fault V_{IL} Low level input voltageOutput disabled0.350.580.81V V_{IL} Low level input voltageOutput disabled0.821.41.95V $V_{I(INT)}$ Intermediate level input voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High state maximum voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High state maximum voltageOutput enabled1.962.643.3V I_{IL} Low level input current (sink) $V_{Enable} = 0 \text{ V}$ -10-30 μA I_{I} High level leakage current for external switch $V_{Enable} = 3.3 \text{ V}$ 1 μA Total numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsTotal deviceImage Bias currentDevice operational1.52mA	I _{Short}	Short-circuit current limit	$R_{Limit} = 22 \Omega$	3.3	4.4	5.5	Α
dv/dtOutput voltage ramp timeEnable to $V_{OUT} = 11.7 \text{ V}$, No $C_{dv/dt}$ 0.50.92.6msEnable/FaultVILLow level input voltageOutput disabled0.350.580.81VVILLow level input voltageOutput disabled0.821.41.95VVIINT)Intermediate level input voltageOutput enabled1.962.643.3VVIIHHigh level input voltageOutput enabled1.962.643.3VVIIMAX)High state maximum voltageOutput enabled1.962.643.3VILLow level input current (sink)VEnable = 0 V-10-30 μA IIHigh level leakage current for external switchVEnable = 3.3 VI1 μA Total numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsTotal numbers of chips that can be connected to this pin for simultaneous shutdown3.52Intermediate levelIntermediate levelDevice operational1.52	I _{Lim}	Overload current limit	$R_{\text{Limit}} = 22 \Omega$		4.4		Α
dv/dtOutput voltage ramp time $C_{dv/dt}$ 0.30.30.92.0misEnable/FaultVILLow level input voltageOutput disabled0.350.580.81VVILLow level input voltageOutput disabled0.821.41.95VVIIIntermediate level input voltageOutput enabled1.962.643.3VVIHHigh level input voltageOutput enabled1.962.643.3VVI(MAX)High state maximum voltageOutput enabled1.962.643.3VILLow level input current (sink)V _{Enable} = 0 V-10-30µAIIHigh level leakage current for external switchV _{Enable} = 3.3 V11µATotal numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsTotal device	dv/dt circu	uit				•	
V_{IL} Low level input voltageOutput disabled0.350.580.81V $V_{I(INT)}$ Intermediate level input voltageThermal fault, output disabled0.821.41.95V V_{IH} High level input voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High state maximum voltage3.44.35.4V I_{IL} Low level input current (sink) $V_{Enable} = 0 V$ -10-30 μA I_{I} High level leakage current for external switch $V_{Enable} = 3.3 V$ 1 μA I_{I} Maximum fan-out for fault signalTotal numbers of chips that can be connected to this pin for simultaneous shutdown3UnitsTotal deviceDevice operational1.52 I_{Bias} Bias currentDevice operational1.52mA	dv/dt	Output voltage ramp time		0.5	0.9	2.6	ms
NLLDescription of the performanceDescription of the performan	Enable/Fa	ult					
VINHigh level input voltageOutput enabled1.962.643.3V $V_{I(MAX)}$ High state maximum voltage 3.4 4.3 5.4 V I_{IL} Low level input current (sink) $V_{Enable} = 0 V$ -10 -30 μA I_{I} High level leakage current for external switch $V_{Enable} = 3.3 V$ -10 -30 μA I_{I} Maximum fan-out for fault signalTotal numbers of chips that can be connected to this pin for simultaneous shutdown 3 UnitsTotal device I_{Bias} Bias currentDevice operational 1.5 2	V _{IL}	Low level input voltage	Output disabled	0.35	0.58	0.81	V
$V_{I(MAX)}$ High state maximum voltage 3.4 4.3 5.4 V I_{IL} Low level input current (sink) $V_{Enable} = 0$ V -10 -30 μ A I_{I} High level leakage current for external switch $V_{Enable} = 3.3$ V 1 μ A Maximum fan-out for fault signal Total numbers of chips that can be connected to this pin for simultaneous shutdown 3 Units Total device I_{Bias} Bias current Device operational 1.5 2 mA	V _{I(INT)}	Intermediate level input voltage	Thermal fault, output disabled	0.82	1.4	1.95	V
Instrume transformed and trans	V _{IH}	High level input voltage	Output enabled	1.96	2.64	3.3	V
II High level leakage current for external switch V _{Enable} = 3.3 V I μA Maximum fan-out for fault signal Total numbers of chips that can be connected to this pin for simultaneous shutdown 3 Units Total device Device operational 1.5 2 mA	V _{I(MAX)}	High state maximum voltage		3.4	4.3	5.4	V
I external switch VEnable 3.3 V I I μA Maximum fan-out for fault signal Total numbers of chips that can be connected to this pin for simultaneous shutdown 3 Units Total device Device operational 1.5 2 mA	Ι _{ΙL}	Low level input current (sink)	V _{Enable} = 0 V		-10	-30	μA
Maximum fan-out for fault signal be connected to this pin for simultaneous shutdown 3 Units Total device Image: Bias current Device operational 1.5 2 mA	lı		V _{Enable} = 3.3 V			1	μA
I _{Bias} Bias current Device operational 1.5 2 mA		Maximum fan-out for fault signal	be connected to this pin for			3	Units
I _{Bias} Bias current mA	Total devic	ce	······································				
		Bias current	Device operational		1.5	2	m۸
	Bias		Thermal shutdown		1		
	6/20		Doc ID 019056 Rev 4				5

 Table 6.
 Electrical characteristics for STEF12

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{min}	Minimum operating voltage				7.6	V
Thermal la	tch					
TSD	Shutdown temperature	(1)		165		°C

 Table 6.
 Electrical characteristics for STEF12 (continued)

1. Pulse test: Pulse width = 300 $\mu s,$ Duty cycle = 2%

2. Guaranteed by design, but not tested in production



5 Typical application

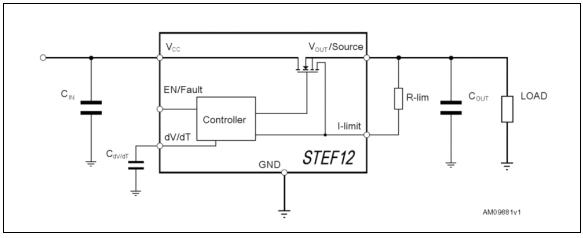
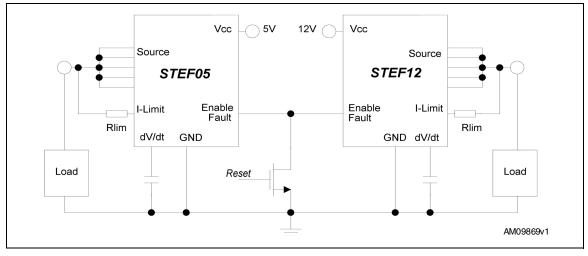




Figure 4. Typical HDD application circuit



5.1 Operating modes

5.1.1 Turn-on

When the input voltage is applied, the Enable/Fault pin goes up to the high state, enabling the internal control circuitry.

After an initial delay time of typically 350 μ s, the output voltage is supplied with a slope defined by the internal dv/dt circuitry. If no additional capacitor is connected to dv/dt pin, the total time from the Enable signal going high and the output voltage reaching the nominal value is around 1 ms (refer to *Figure 5, 15*)



5.1.2 Normal operating condition

The STEF12 E-fuse behaves like a mechanical fuse, buffering the circuitry on its output with the same voltage shown at its input, with a small voltage fall due to the N-channel MOSFET R_{DSOn} .

5.1.3 Output voltage clamp

This internal protection circuit clamps the output voltage to a maximum safe value, typically 15 V, if the input voltage exceeds this threshold.

5.1.4 Current limiting

When an overload event occurs, the current limiting circuit reduces the conductivity of the power MOSFET, in order to clamp the output current at the value selected externally by means of the limiting resistor R_{Limit} (*Figure 3*).

5.1.5 Thermal shutdown

If the device temperature exceeds the thermal latch threshold, typically 165 °C, the thermal shutdown circuitry turns the power MOSFET off, thus disconnecting the load. The EN/Fault pin of the device is automatically set at an intermediate voltage, in order to signal the overtemperature event. In this condition the E-fuse can be reset either by cycling the supply voltage or by pulling down the EN pin below the V_{il} threshold and then releasing it.

5.2 R limit calculation

As shown in *Figure 3*, the device uses an internal N-channel sense FET with a fixed ratio, to monitor the output current and limit it at the level set by the user.

The R_{Limit} value for achieving the requested current limitation can be estimated by using the following theoretical formula, together with the graph in *Figure 13: Current limit vs. RLimit*.

Equation 1

$$\mathsf{RLimit} = \frac{95}{\mathsf{IShort}}$$

5.3 C_{dv/dt} calculation

Connecting a capacitor between the $C_{dv/dt}$ pin and GND allows the modification of the output voltage ramp-up time.

Given the desired time interval Δt during which the output voltage goes from zero to its maximum value, the capacitance to be added on the $C_{dv/dt}$ pin can be calculated using the following theoretical formula:

Equation 2

$$C_{dvdt} = 24 \times 10^{-9} \Delta t - 30 \times 10^{-12}$$

Where $C_{dv/dt}$ is expressed in Farads and the time in seconds.

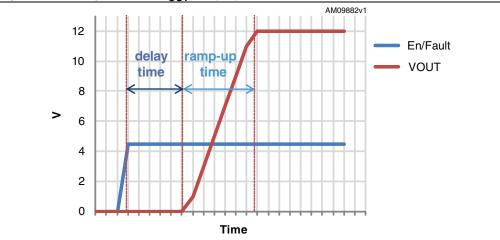


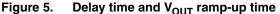
The addition of an external $C_{dv/dt}$ influences also the initial delay time, defined as the time between the Enable signal going high and the start of the V_{OUT} slope (*Figure 5*).

The contribution of the external capacitor to this time interval can be estimated by using the following theoretical formula:

Equation 3

delay time =
$$350 \times 10^{-6} + 11.3 \times 10^{6} \times C_{dvdt}$$





5.4 Enable/Fault pin

The Enable/Fault pin has the dual function of controlling the output of the device and, at the same time, of providing information about the device status to the application.

When it is used as a standard Enable pin, it should be connected to an external open-drain or open-collector device. In this case, when it is pulled at low logic level, it turns the output of the E-Fuse off.

If this pin is left floating, since it has internal pull-up circuitry, the output of the E-Fuse is kept ON, in normal operating conditions.

In case of thermal fault, the pin is pulled to an intermediate state (*Figure 6*). This signal can be provided to a monitor circuit, informing it that a thermal shutdown has occurred, or it can be directly connected to the Enable/Fault pins of other STEFxx devices on the same application in order to achieve a simultaneous enable/disable feature.

When a thermal fault occurs, the device can be reset either by cycling the supply voltage or by pulling down the Enable pin below the V_{il} threshold and then releasing it.



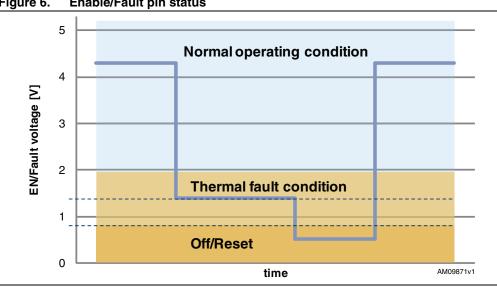


Figure 6. Enable/Fault pin status



The following plots are referred to the typical application circuit and, unless otherwise noted, at $T_A = 25$ °C.

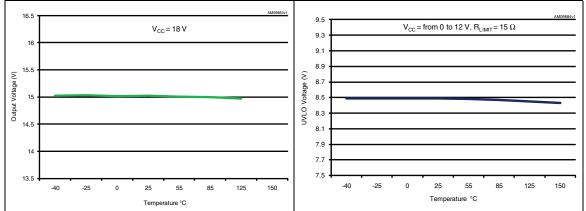
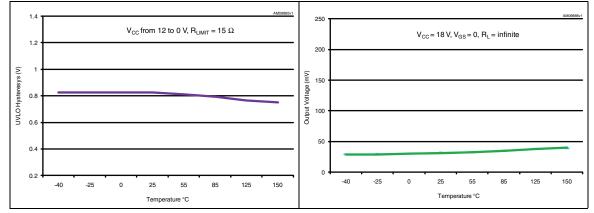


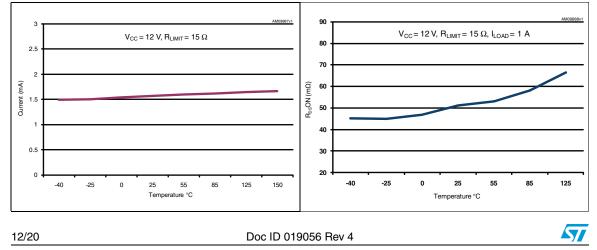
Figure 7. Clamping voltage vs. temperature Figure 8. UVLO voltage vs. temperature



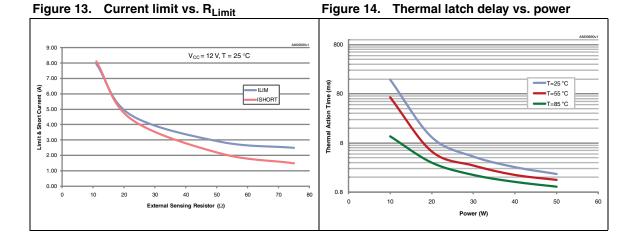












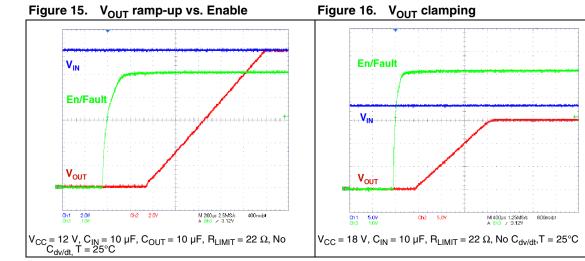
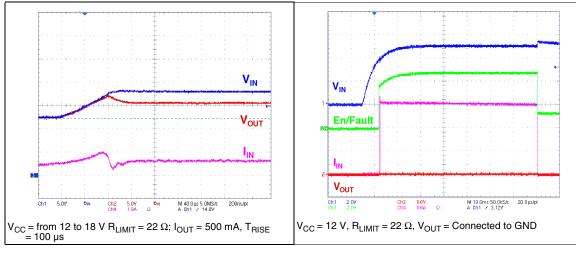


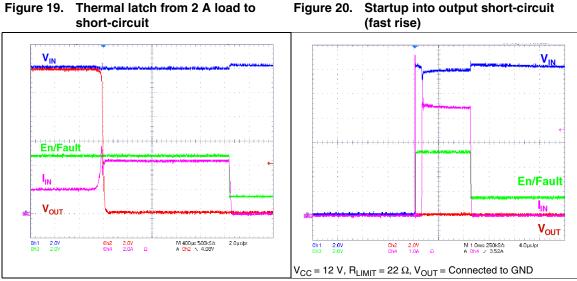


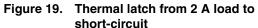
Figure 18. Startup into output short-circuit



Doc ID 019056 Rev 4

57





14/20



7 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

Dim.		mm.	
Dini.	Min.	Тур.	Max.
А	0.80	0.90	1.00
A1		0.02	0.05
A2	0.55	0.65	0.80
A3		0.20	
b	0.18	0.25	0.30
D	2.85	3.00	3.15
D2	2.20		2.70
E	2.85	3.00	3.15
E2	1.40		1.75
е		0.50	
L	0.30	0.40	0.50
ddd			0.08

Table 7. DFN10L (3x3 mm.) mechanical data



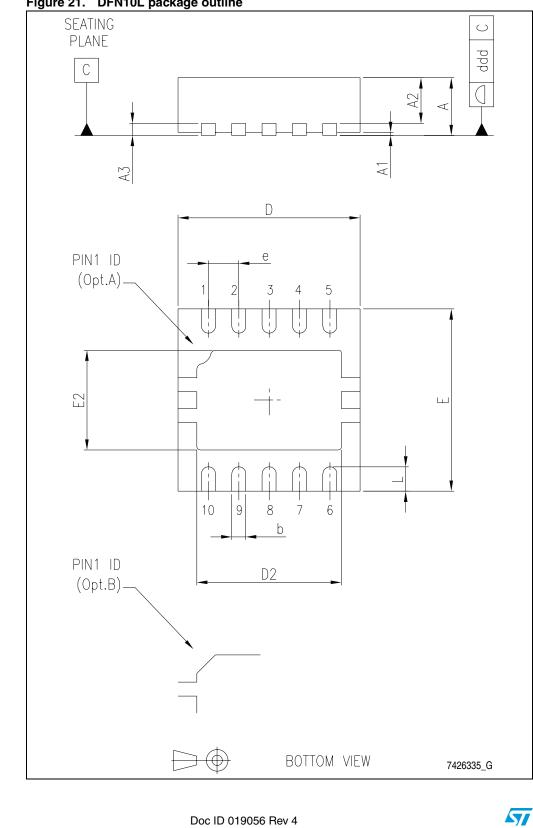
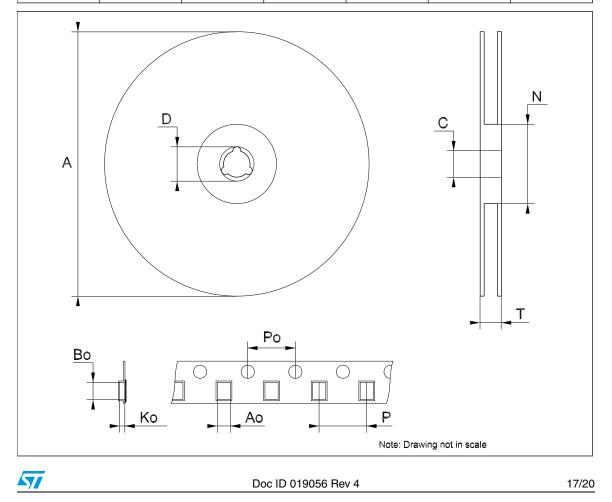


Figure 21. DFN10L package outline

16/20

٦

Dim.		mm.			inch.	
Dini.	Min.	Тур.	Max.	Min.	Тур.	Max.
А			180			7.087
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			14.4			0.567
Ao		3.3			0.130	
Во		3.3			0.130	
Ko		1.1			0.043	
Po		4			0.157	



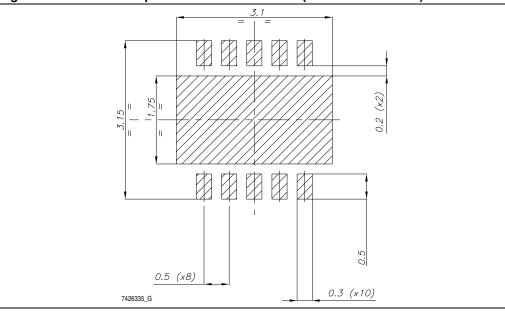


Figure 22. DFN10L footprint - recommended data (dimensions in mm.)

18/20



8 Revision history

Date	Revision	Changes	
15-Jul-2011	1	Initial release.	
08-Aug-2011	2	Modified definition for T _{op} in <i>Table 3: Absolute maximum ratings</i> .	
14-Dec-2011	3	Removed $V_{dv/dt}$ and $I_{dv/dt}$ rows from dv/dt circuit <i>Table 6 on page 6</i> .	
06-Mar-2012	4	Updated: package mechanical data <i>Table 7 on page 15</i> , <i>Figure 21 on page 16</i> and <i>Figure 22 on page 18</i> .	

Table 8. Document revision history



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

20/20

